



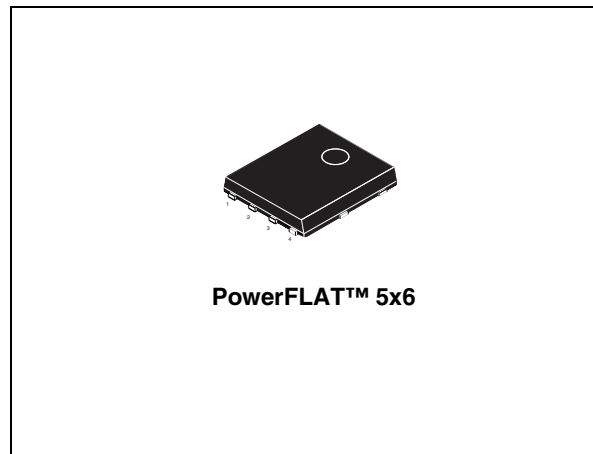
STL120N2VH5

N-channel 20 V, 0.002 Ω , 28 A STripFET™ V Power MOSFET in PowerFLAT™ 5x6 package

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D
STL120N2VH5	20 V	< 0.003 Ω	28 A

- Improved die-to-footprint ratio
- Very low profile package
- Very low thermal resistance
- Conduction losses reduced
- Switching losses reduced
- 2.5 V gate drive
- Very low threshold device



Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™V technology. The device has been optimized to achieve very low on-state resistance, contributing to an FOM that is among the best in its class.

Figure 1. Internal schematic diagram

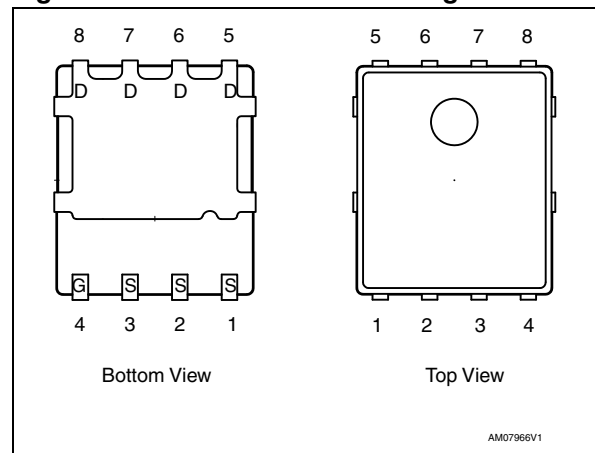


Table 1. Device summary

Order code	Marking	Package	Packaging
STL120N2VH5	120N2VH5	PowerFLAT™ 5x6	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuits	8
4	Package mechanical data	9
5	Packaging mechanical data	15
6	Revision history	17

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	20	V
V_{GS}	Gate-source voltage	± 8	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ °C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ °C}$	75	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ °C}$	28	A
$I_{DM}^{(2),(3)}$	Drain current (pulsed)	112	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ °C}$	80	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ °C}$	4	W
	Derating factor ⁽²⁾	0.03	W/°C
T_j T_{stg}	Operating junction temperature storage temperature	- 55 to 150	°C

1. The value is rated according to Rthj-case
2. When mounted on FR-4 board of 1in², 2oz Cu. t < 10 sec
3. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	1.56	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max.	31.25	°C/W

1. When mounted on FR-4 board of 1in², 2oz Cu. t < 10 sec

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	20	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 14\text{ V}$)	300	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	20			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 20\text{ V}$ $V_{DS} = 20\text{ V}$, $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 8\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.70			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 4.5\text{ V}$, $I_D = 14\text{ A}$ $V_{GS} = 2.5\text{ V}$, $I_D = 14\text{ A}$		0.002 0.0028	0.003 0.004	Ω Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	4660	-	μF
C_{oss}	Output capacitance			870		
C_{rss}	Reverse transfer capacitance			130		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 10\text{ V}$, $I_D = 14\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 4.5\text{ V}$ (see Figure 13)	-	21	-	ns
t_r	Rise time			60		
$t_{d(off)}$	Turn-off delay time			76		
t_f	Fall time			55		
Q_g	Total gate charge	$V_{DD} = 10\text{ V}$, $I_D = 28\text{ A}$, $V_{GS} = 2.5\text{ V}$ (see Figure 14)	-	29	-	nC
Q_{gs}	Gate-source charge			9.8		
Q_{gd}	Gate-drain charge			13		

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		28 112	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 28 \text{ A}$, $V_{GS} = 0$	-		1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 28 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 16 \text{ V}$ (see Figure 15)	-	34 30 1.4		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 28 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 16 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 15)	-	35 31 1.8		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

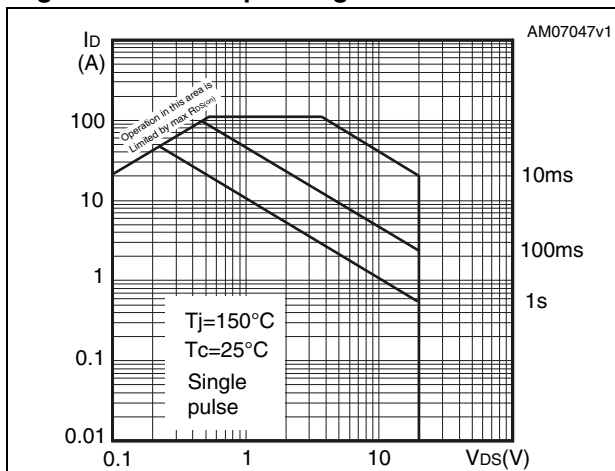


Figure 3. Thermal impedance

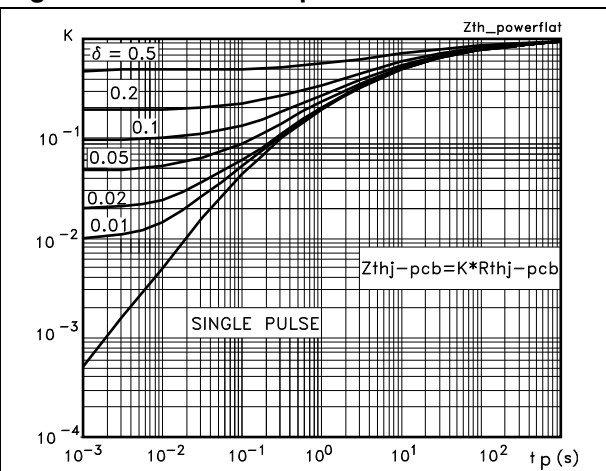


Figure 4. Output characteristics

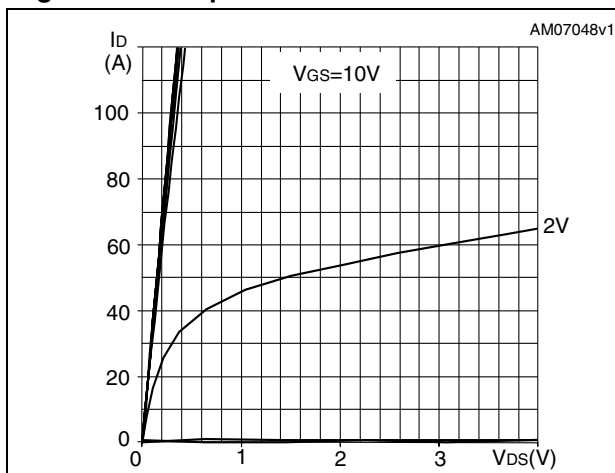


Figure 5. Transfer characteristics

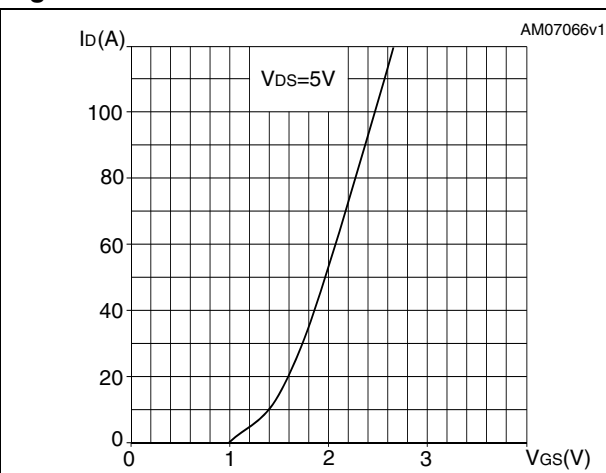


Figure 6. Normalized BV_{DSS} vs temperature

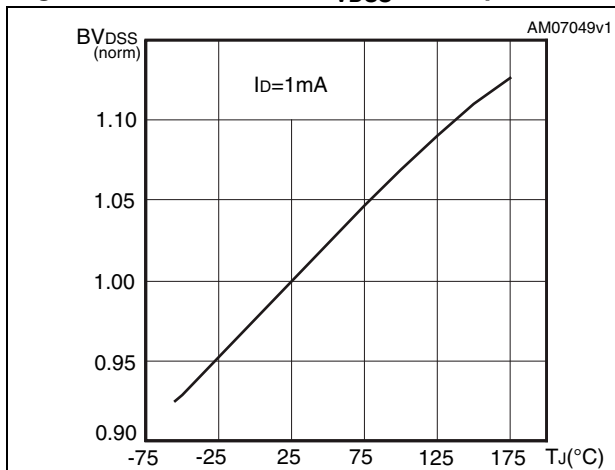


Figure 7. Static drain-source on resistance

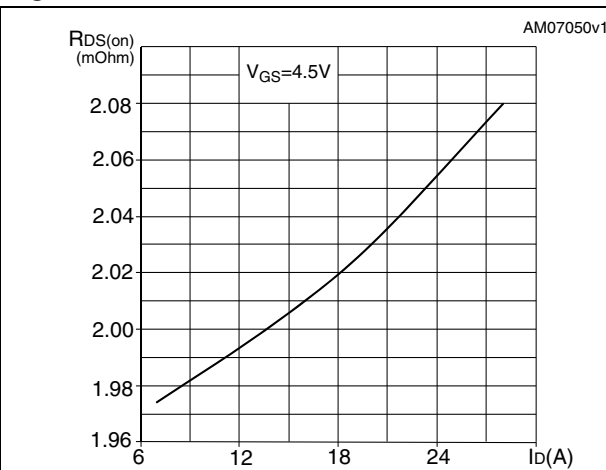


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

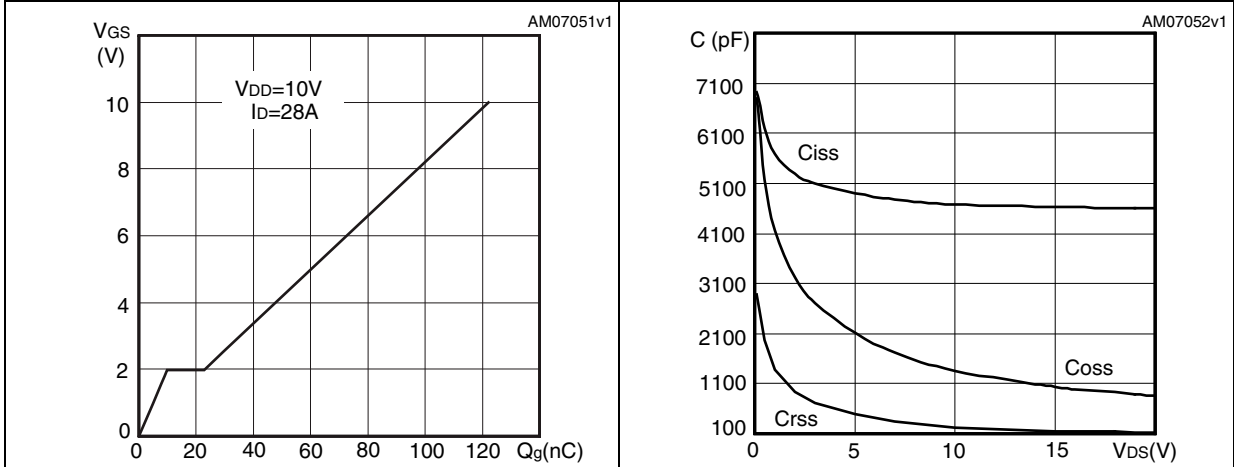


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

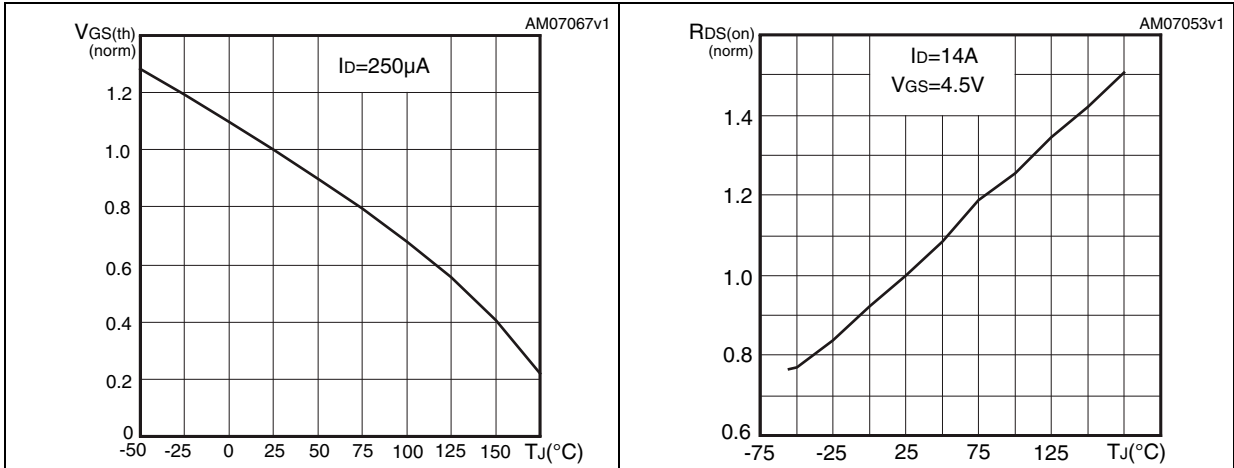
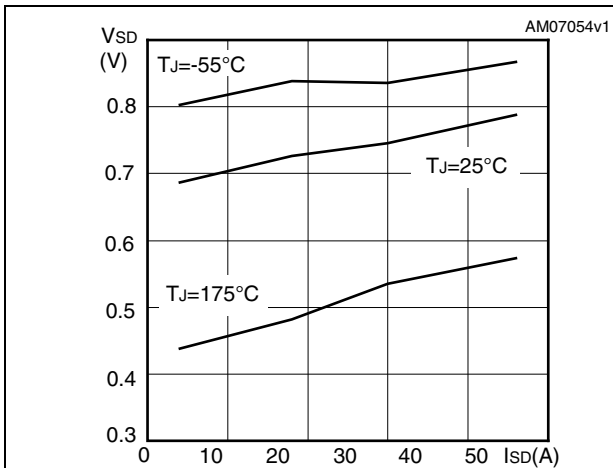
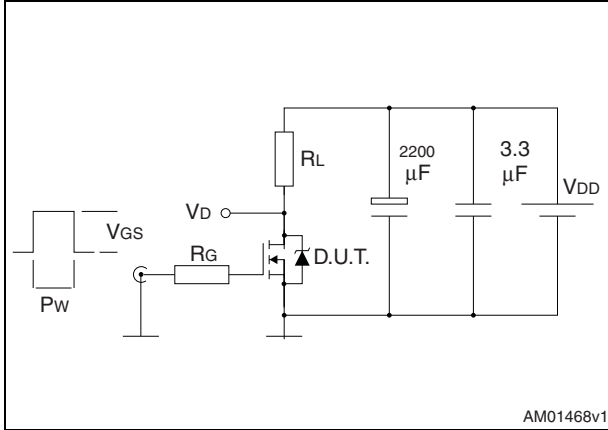


Figure 12. Source-drain diode forward characteristics



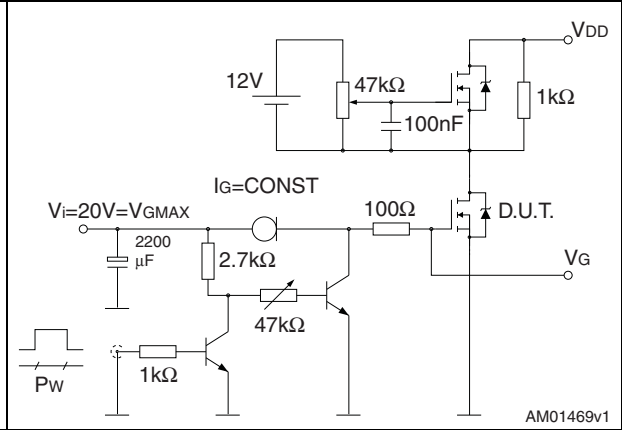
3 Test circuits

Figure 13. Switching times test circuit for resistive load



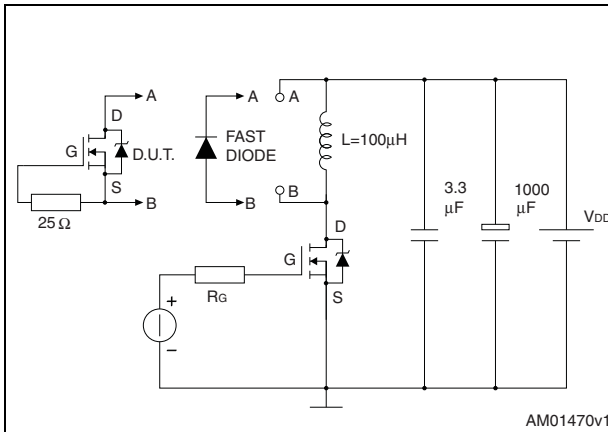
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Figure 14. Gate charge test circuit



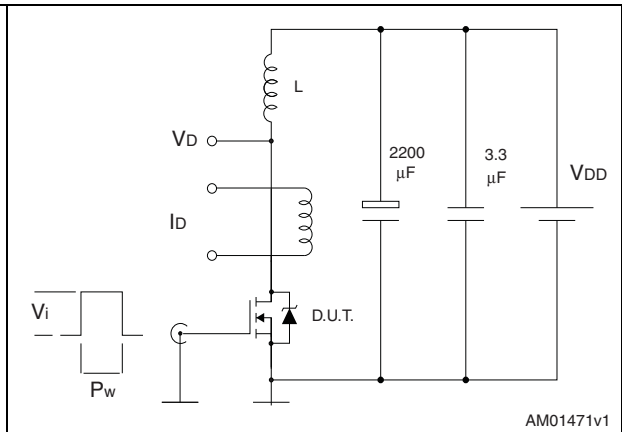
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Figure 15. Test circuit for inductive load switching and diode recovery times



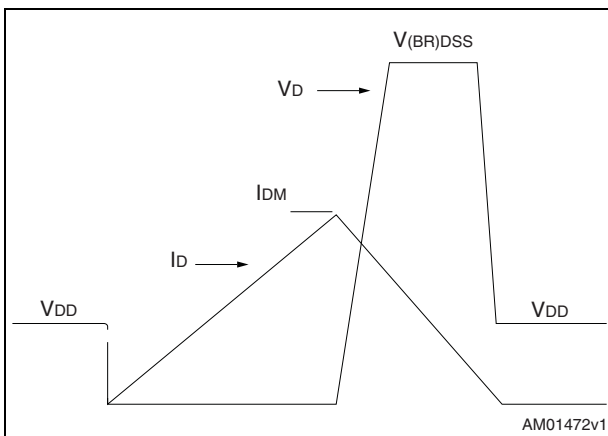
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Figure 16. Unclamped inductive load test circuit



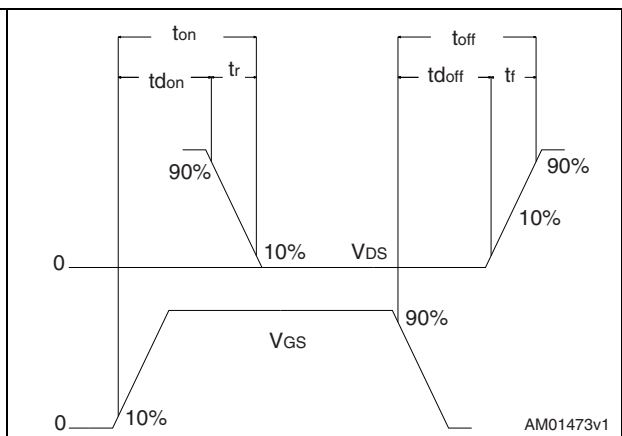
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform



AM01473v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. PowerFLAT™ 5x6 type C-B mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.83	0.93
A1	0	0.02	0.05
A3		0.20	
b	0.35	0.40	0.47
D		5.00	
D1		4.75	
D2	4.15	4.20	4.25
E		6.00	
E1		5.75	
E2	3.43	3.48	3.53
E4	2.58	2.63	2.68
e		1.27	
L	0.70	0.80	0.90

Figure 19. PowerFLAT™ 5x6 type C-B drawing

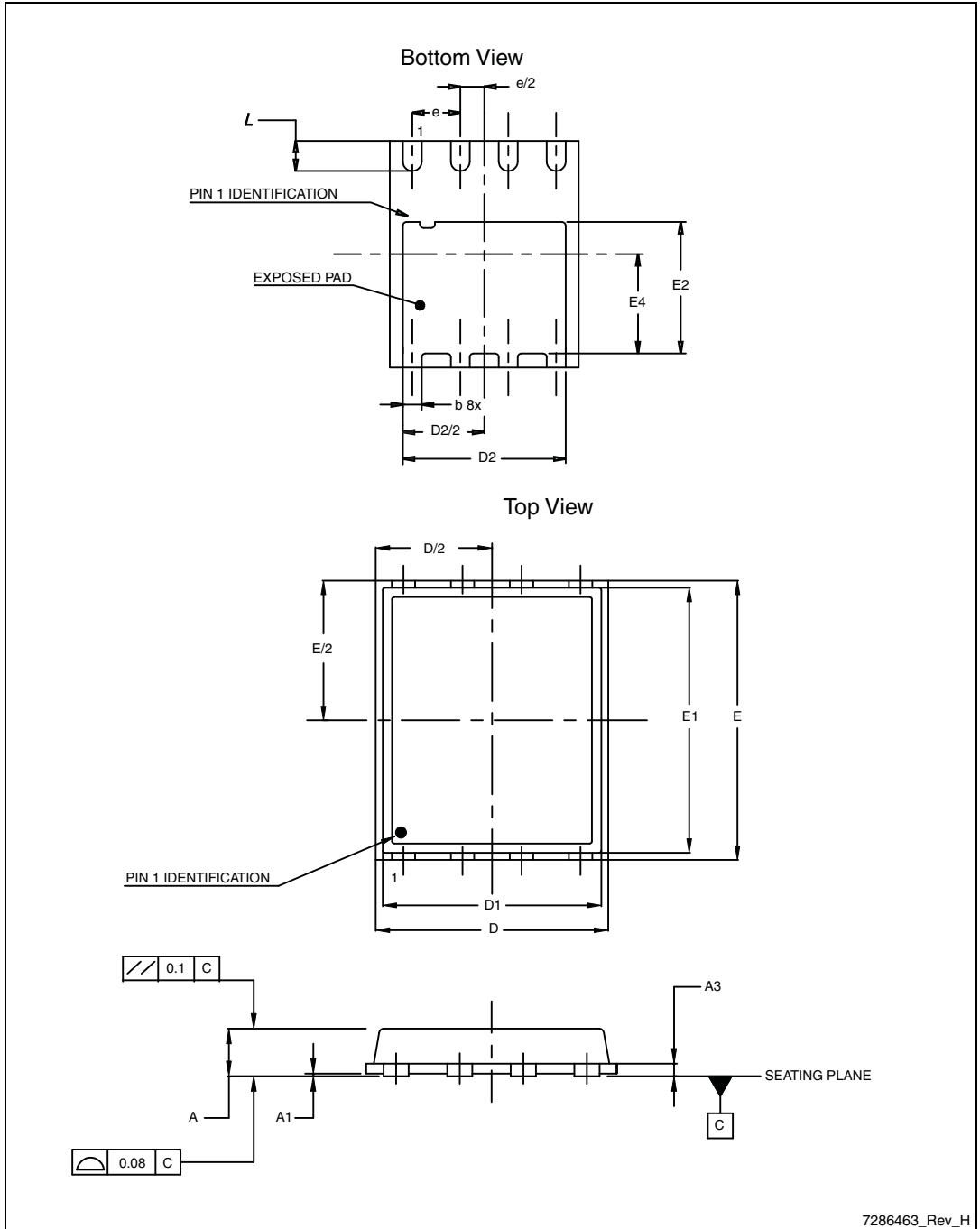


Table 9. PowerFLAT™ 5x6 type S-C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Figure 20. PowerFLAT™ 5x6 type S-C mechanical data

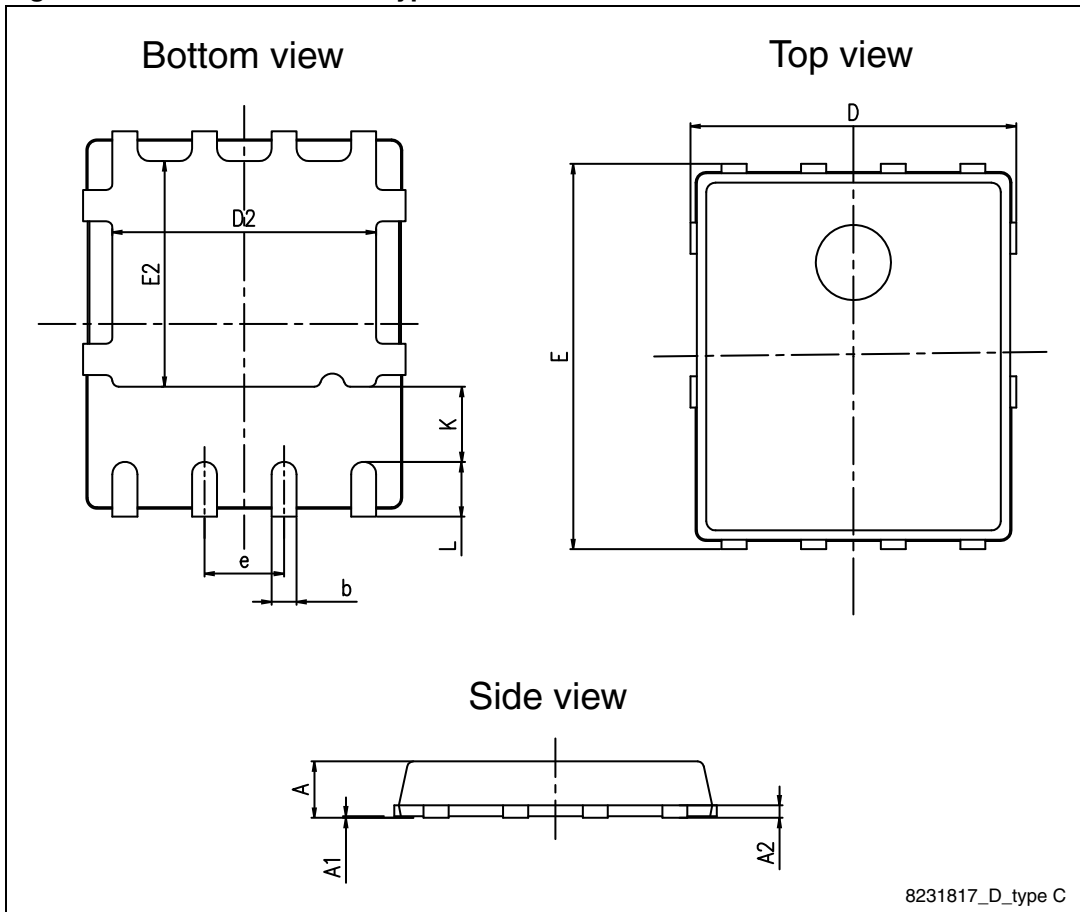
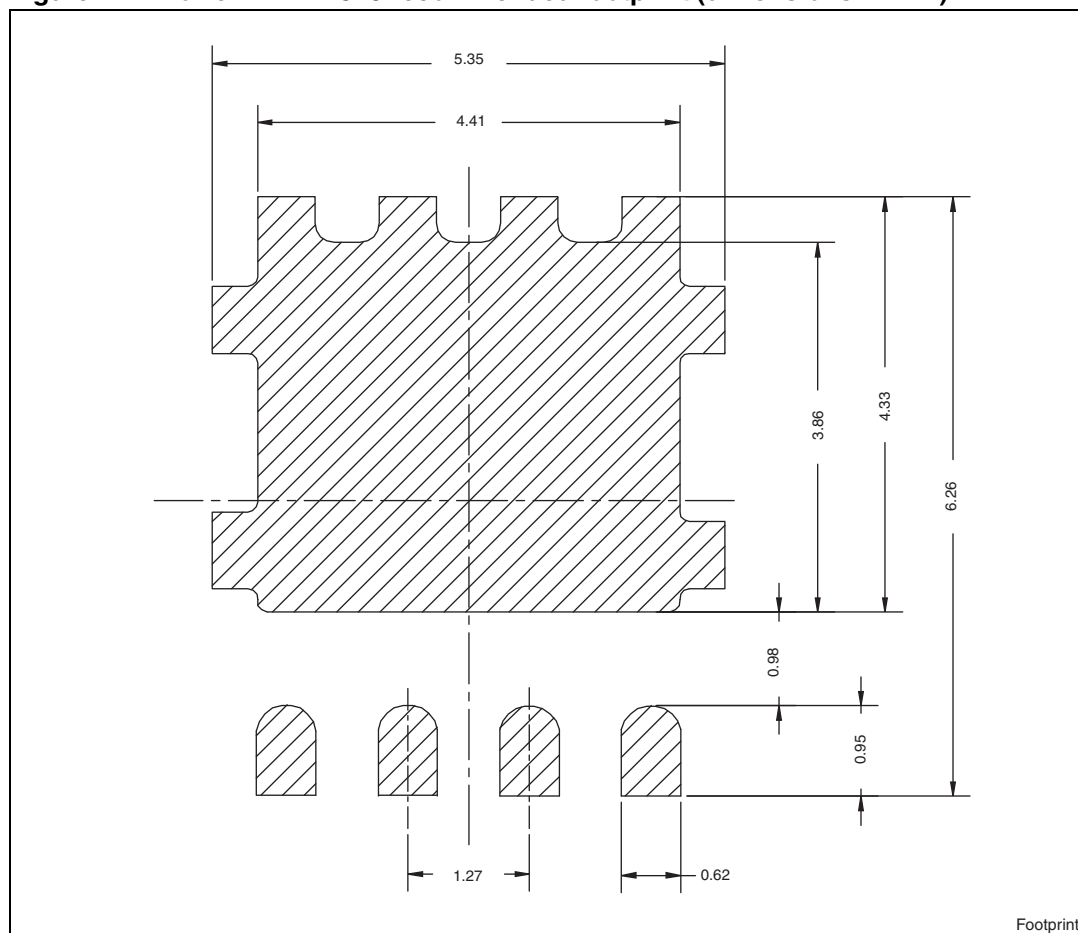


Figure 21. PowerFLAT™ 5x6 recommended footprint (dimensions in mm)



5 Packaging mechanical data

Figure 22. PowerFLAT™ 5x6 tape

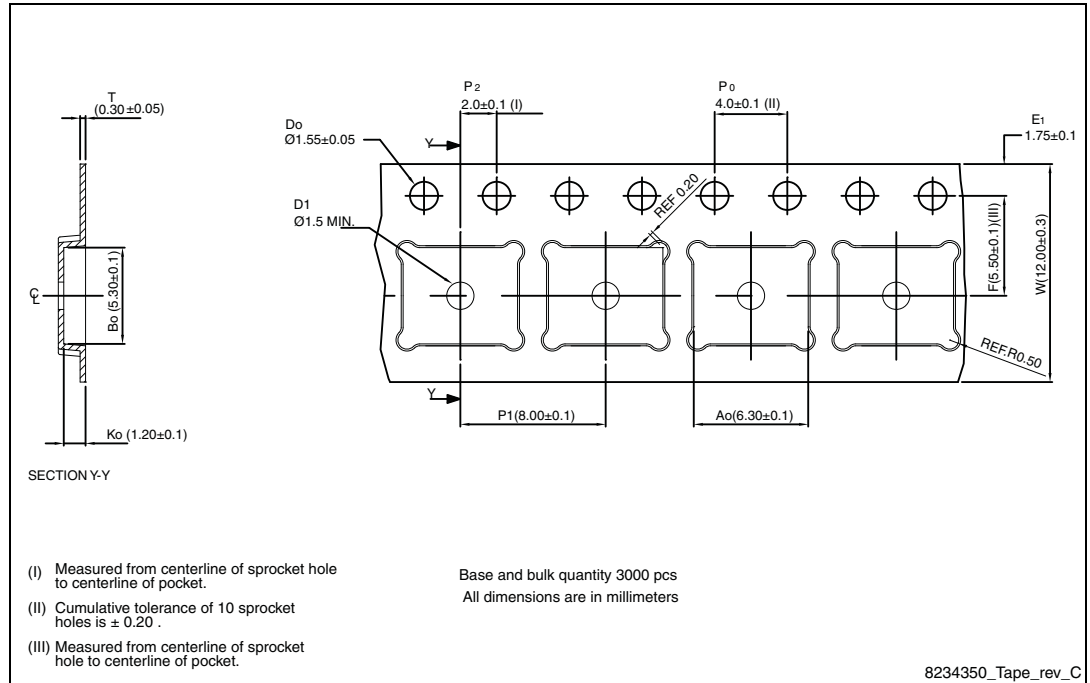


Figure 23. PowerFLAT™ 5x6 package orientation in carrier tape.

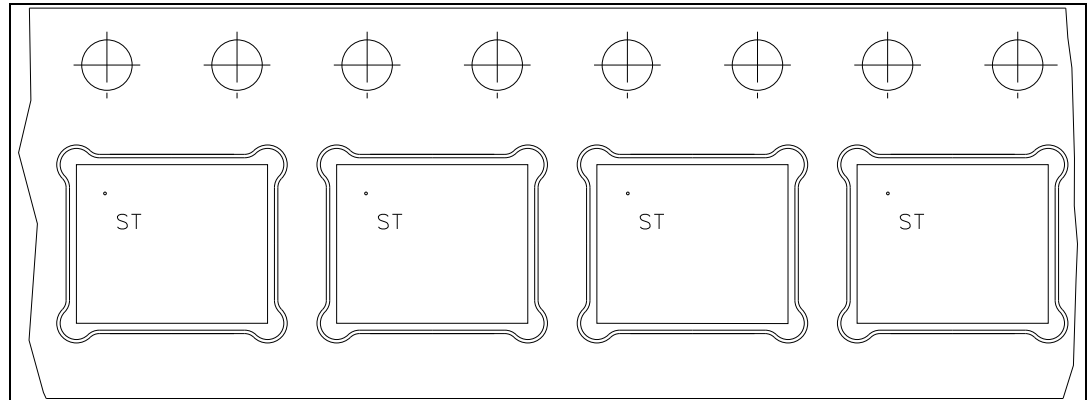
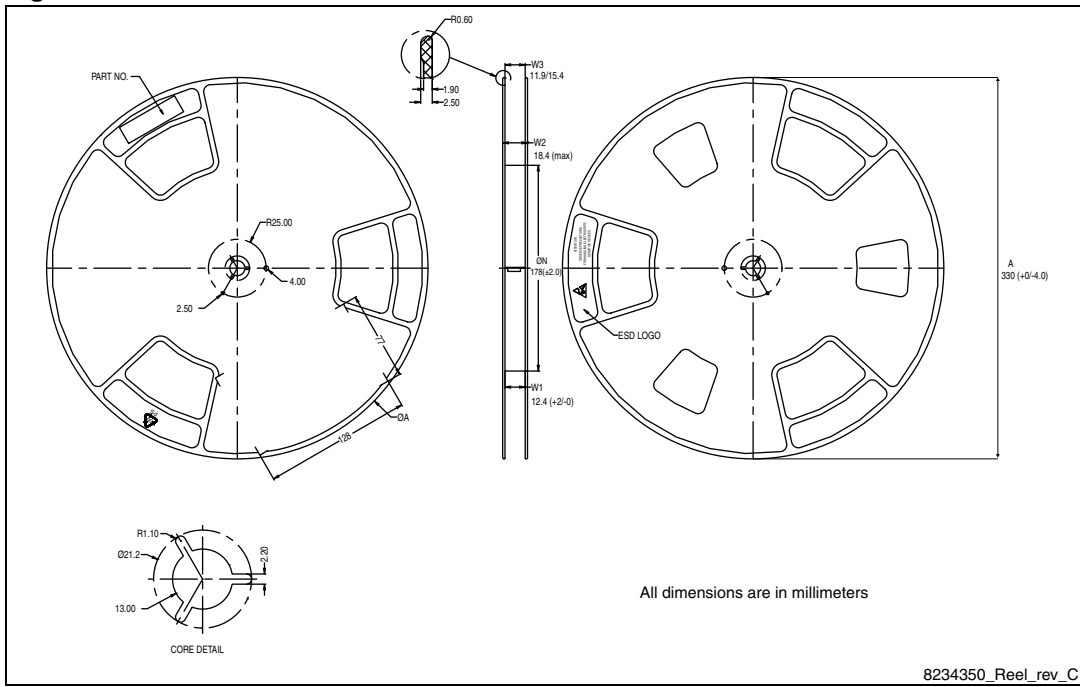


Figure 24. PowerFLAT™ 5x6 reel



6 Revision history

Table 10. Document revision history

Date	Revision	Changes
20-Apr-2009	1	First issue.
01-Mar-2012	2	Document status promoted from preliminary data to datasheet <i>Section 4: Package mechanical data</i> has been modified: – <i>Table 8: PowerFLAT™ 5x6 type C-B mechanical data</i> , <i>Table 9: PowerFLAT™ 5x6 type S-C mechanical data</i> , <i>Figure 19: PowerFLAT™ 5x6 type C-B drawing</i> , <i>Figure 20:</i> <i>PowerFLAT™ 5x6 type S-C mechanical data</i> and <i>Figure 21:</i> <i>PowerFLAT™ 5x6 recommended footprint (dimensions in mm)</i> have been added.

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